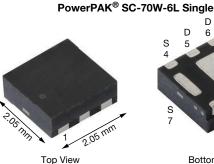
SQAA42CEJW

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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



Marking Code: QAExxx



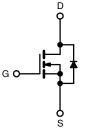
Bottom View

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.030			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.046			
I _D (A)	10			
Configuration	Single			

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- Wettable flank terminals
- 100 % R_{α} and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SC-70W-6L
Lead (Pb)-free and halogen-free	SQAA42CEJW (for detailed order number please see www.visbay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \degree C$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	T _C = 25 °C ª	1	10		
	T _C = 125 °C	I _D	8.8		
Continuous source current (diode conduction) a		I _S	10	А	
Pulsed drain current ^b		I _{DM}	40		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	10.5		
Single pulse avalanche energy		E _{AS}	5.51	mJ	
Maximum power dissipation	T _C = 25 °C	PD	13.6	w	
	T _C = 125 °C	PD	4.5	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	90	°C/W
Junction-to-case (drain)			11	0/10

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

S23-0817-Rev. A, 09-Oct-2023

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SQAA42CEJW

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•			
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		1.5	2.0	2.5	v	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	Α	
Drain-source on-state resistance ^a		V _{GS} = 10 V	I _D = 4.5 A	-	0.0234	0.030		
	P	V _{GS} = 10 V	I _D = 4.5 A, T _J = 125 °C	-	-	0.0472	Ω	
	R _{DS(on)}	V _{GS} = 10 V	l _D = 4.5 A, T _J = 175 °C	-	-	0.0582		
		V _{GS} = 4.5 V	I _D = 3 A	-	0.0360	0.046		
Forward transconductance b	g _{fs}	V _{DS} :	= 15 V, I _D = 4.5 A	-	16	-	S	
Dynamic ^b					•			
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	420	590	pF	
Output capacitance	Coss			-	160	230		
Reverse transfer capacitance	C _{rss}			-	13	22		
Total gate charge ^c	Qg			-	7.5	12	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, I_D = 6 \text{ A}$	-	1.9	-		
Gate-drain charge ^c	Q _{gd}			-	1.3	-		
Gate resistance	Rg	f = 1 MHz		0.5	0.96	1.5	Ω	
Turn-on delay time ^c	t _{d(on)}			-	7	12		
Rise time ^c	t _r	V _{DD} =	= 30 V, R_L = 12 Ω	-	3	6	1	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 2.5 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	13	20	- ns	
Fall time ^c	t _f			-	3	6		
Source-Drain Diode Ratings and Charact	eristics ^b							
Pulsed current ^a	I _{SM}			-	-	40	А	
Forward voltage	V _{SD}	I _F = 4.5 A, V _{GS} = 0 V		-	0.85	1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = 2 A, di/dt = 100 A/μs		-	16	32	ns	
Body diode reverse recovery charge	Q _{rr}			-	8	16	nC	
Reverse recovery fall time	ta			-	9	-		
Reverse recovery rise time	t _b			-	7	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.9	-	А	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

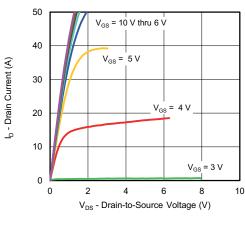
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

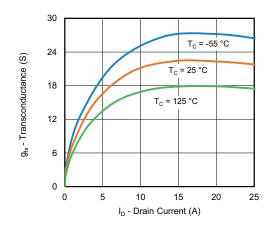


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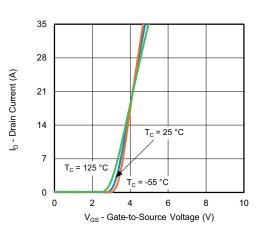
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



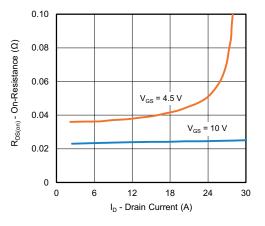
Output Characteristics



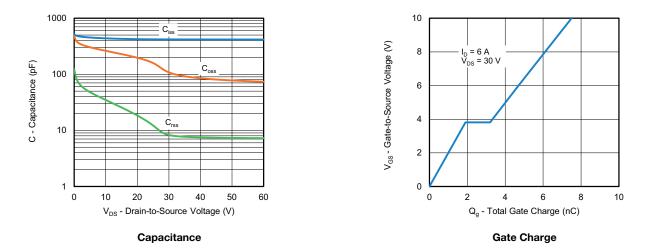
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



S23-0817-Rev. A, 09-Oct-2023

3

Document Number: 62411

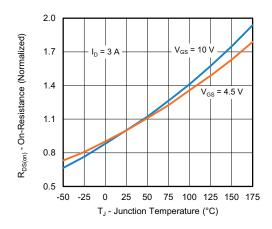
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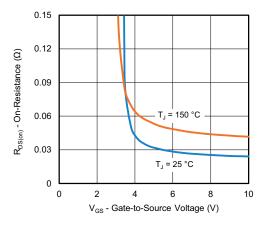
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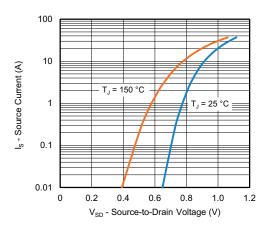
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



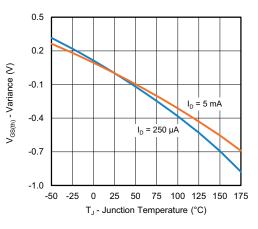
On-Resistance vs. Junction Temperature



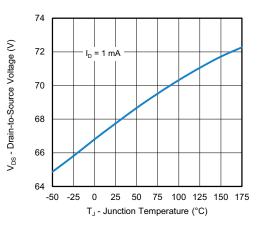
On-Resistance vs. Gate-to-Source Voltage



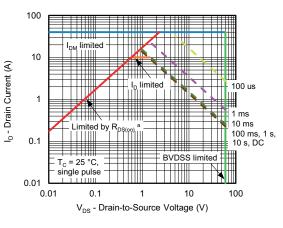
Source Drain Diode Forward Voltage



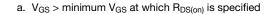
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



Safe Operating Area



S23-0817-Rev. A, 09-Oct-2023

4

Note

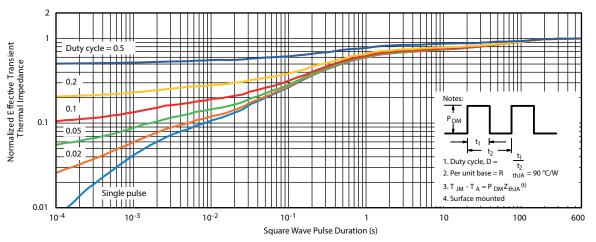
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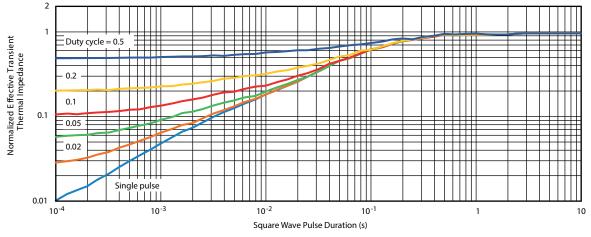


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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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